

**isc Silicon PNP Darlington Power Transistor**

**MJ4032**

**DESCRIPTION**

- With TO-3 package
- Respectively complement to type MJ4035
- DARLINGTON
- High DC current gain

**APPLICATIONS**

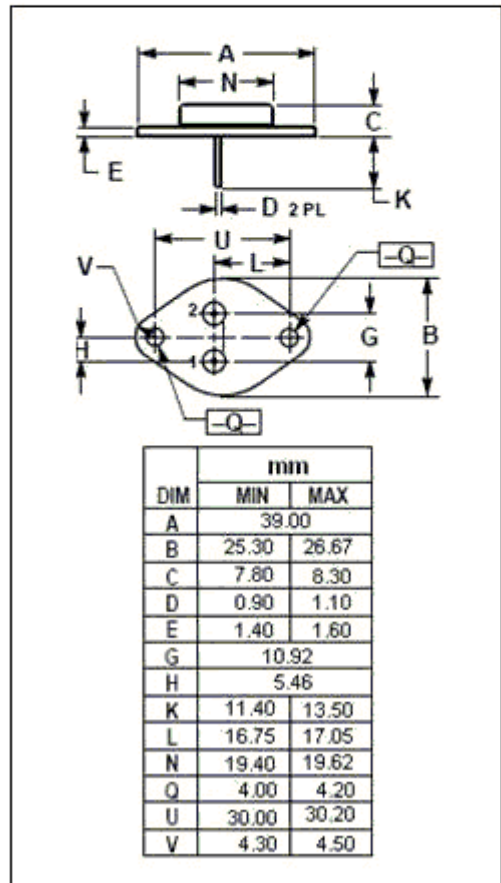
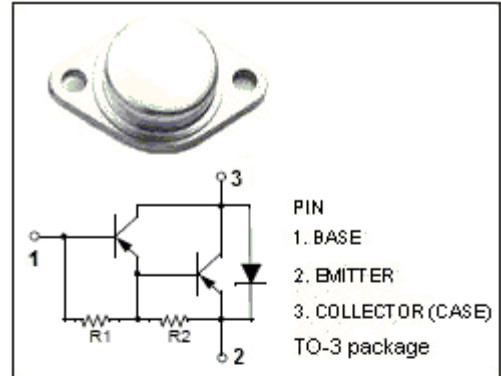
- For use as output devices in complementary general purpose amplifier applications.

**ABSOLUTE MAXIMUM RATINGS(T<sub>C</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-100	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-16	A
I <sub>B</sub>	Base Current	-0.5	A
P <sub>C</sub>	Collector Power Dissipation@T <sub>C</sub> =25°C	150	W
T <sub>J</sub>	Junction Temperature	200	°C
T <sub>stg</sub>	Storage Temperature	-55~200	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.17	°C/W



**isc Silicon PNP Darlington Power Transistor****MJ4032****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C=-100\text{mA}; I_B=0$	-100		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=-10\text{A}; I_B=-40\text{mA}$		-2.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=-16\text{A}; I_B=-80\text{mA}$		-4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=-5\text{A}; I_B=-400\text{mA}$		-3	V
$V_{BE(on)}$	Base-Emitter On voltage	$I_C=-10\text{A}; V_{CE}=-3\text{V}$		-3	V
$I_{CER}$	Collector Cutoff Current	$V_{CB}=-100\text{V}; R_{BE}=1\text{K}\Omega$ ; $V_{CB}=-100\text{V}; R_{BE}=1\text{K}\Omega; T_C=150^{\circ}\text{C}$		-1 -5	mA
$I_{CEO}$	Collector Cutoff current	$V_{CE}=-50\text{V}; I_B=0$		-3	mA
$I_{EBO}$	Emitter Cut-off current	$V_{EB}=-5\text{V}; I_C=0$		-5	mA
$h_{FE}$	DC Current Gain	$I_C=-10\text{A}; V_{CE}=-3\text{V}$	1000		